

## 3A, 12V, Synchronous-Rectified Buck Converter

#### **Features**

- Wide Input Voltage from 4.3V to 14V
- Output Current up to 3A
- Adjustable Output Voltage from 0.8V to V<sub>IN</sub>
  - ±2% System Accuracy
- 55mWIntegrated Power MOSFETs
- High Efficiency up to 95%
  - Automatic Skip/PWM Mode Operation
- Current-Mode Operation
  - Easy Feedback Compensation
  - Stable with Low ESR Output Capacitors
  - Fast Load/Line Transient Response
- Power-On-Reset Monitoring
- Fixed 500kHz Switching Frequency in PWM Mode
- Built-In Digital Soft-Start and Soft-Stop
- Current-Limit Protection with Frequency Foldback
- 123% Over-Voltage Protection
- Hiccup-Mode 50% Under-Voltage Protection
- Over-Temperature Protection
- <3mA Quiescent Current in Shutdown Mode</li>
- SOP-8P and Compact 4mmx4mm DFN-8 (DFN4x4-8) Packages
- Lead Free and Green Devices Available (RoHS Compliant)

# **Applications**

- OLPC, UMPC
- Notebook Computer
- · Handheld Portable Device
- Step-Down Converters Requiring High Efficiency and 3A Output Current

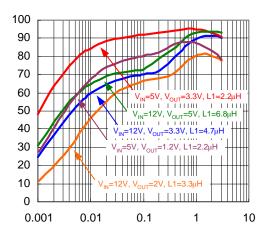
## **General Description**

The APW7145 is a 3A synchronous-rectified Buck converter with integrated  $55m\Omega$  power MOSFETs. The APW7145, designed with a current-mode control scheme, can convert wide input voltage of 4.3V to 14V to the output voltage adjustable from 0.8V to VIN to provide excellent output voltage regulation.

For high efficiency over all load current range, the APW7145 is equipped with an automatic Skip/PWM mode operation. At light load, the IC operates in the Skip mode, which keeps a constant minimum inductor peak current, to reduce switching losses. At heavy load, the IC works in PWM mode, which inductor peak current is programmed by the COMP voltage, to provide high efficiency and excellent output voltage regulation.

The APW7145 is also equipped with power-on-reset, soft-start, soft-stop, and whole protections (under-voltage, over-voltage, over-temperature, and current-limit) into a single package. In shutdown mode, the supply current drops below  $3\mu A$ .

This device, available SOP-8P and DFN4x4-8 packages, provides a very compact system solution with minimal external components and PCB area.



ANPEC reserves the right to make changes to improve reliability or manufacturability without notice, and advise customers to obtain the latest version of relevant information to verify before placing orders.

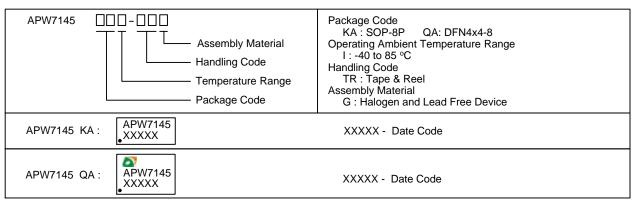


## Pin Configuration



The Pin 7 must be connected to the Exposed Pad

## **Ordering and Marking Information**



Note: ANPEC lead-free products contain molding compounds/die attach materials and 100% matte tin plate termination finish; which are fully compliant with RoHS. ANPEC lead-free products meet or exceed the lead-free requirements of IPC/JEDEC J-STD-020D for MSL classification at lead-free peak reflow temperature. ANPEC defines "Green" to mean lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500ppm by weight).

# **Absolute Maximum Ratings** (Note 1)

Symbol	Parameter	Parameter			
V <sub>IN</sub>	VIN Supply Voltage (VIN to AGND)		-0.3 ~ 15	V	
M	LV to CND Voltage	> 100ns	-1 ~ V <sub>IN</sub> +1	V	
$V_{LX}$	LX to GND Voltage	< 100ns	- 5 ~ V <sub>IN</sub> +5	7 °	
	PGND to AGND Voltage	PGND to AGND Voltage			
	EN to AGND Voltage		-0.3 ~ V <sub>IN</sub> +0.3	V	
	FB, COMP to AGND Voltage		-0.3 ~ 6	V	
P <sub>D</sub>	Power Dissipation		Internally Limited	W	
	Maximum Junction Temperature	150	°C		
T <sub>STG</sub>	Storage Temperature	-65 ~ 150	°C		
T <sub>SDR</sub>	Maximum Lead Soldering Temperature, 10 Sec	260	°C		

Note1: Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability



## **Thermal Characteristics**

Symbol	Parameter		Typical Value	Unit
$\theta_{\sf JA}$		SOP-8P FN4x4-8	50 65	°C/W
θЈС		SOP-8P FN4x4-8	20 30	°C/W

Note 2:  $\theta_{JA}$  is measured with the component mounted on a high effective thermal conductivity test board in free air.

# **Recommended Operating Conditions** (Note 4)

Symbol	Parameter	Range	Unit
V <sub>IN</sub>	VIN Supply Voltage	4.3 ~ 14	V
V <sub>OUT</sub>	Converter Output Voltage	0.8 ~ V <sub>IN</sub>	V
I <sub>OUT</sub>	Converter Output Current	0 ~ 3	Α
C <sub>IN</sub>	Converter Input Capacitor (MLCC)	8 ~ 50	μF
C <sub>OUT</sub>	Converter Output Capacitor	20 ~ 1000	μF
Cour	Effective Series Resistance	0 ~ 60	mΩ
L <sub>OUT</sub>	Converter Output Inductor	1 ~ 22	μН
	Resistance of the Feedback Resistor connected from FB to GND	1 ~ 20	kΩ
T <sub>A</sub>	Ambient Temperature	-40 ~ 85	°C
TJ	Junction Temperature	-40 ~ 125	°C

Note 4: Refer to the Typical Application Circuits.

## **Electrical Characteristics**

Refer to the "Typical Application Circuits". These specifications apply over  $V_{IN}$ =12V,  $V_{OUT}$ =3.3V and  $T_A$ = -40 ~ 85°C, unless otherwise specified. Typical values are at  $T_A$ =25°C.

Symbol	Parameter	Test Conditions		Unit			
Syllibol	Farameter	rest conditions	Min.	Тур.	Max.	Oille	
SUPPLY CUR	RENT	•	,	,			
I <sub>VIN</sub>	VIN Supply Current	$V_{FB} = V_{REF}$ +50mV, $V_{EN}$ =3V, LX=NC	-	0.5	1.5	mA	
I <sub>VIN_SD</sub>	VIN Shutdown Supply Current	V <sub>EN</sub> = 0V	-	-	3	μΑ	
POWER-ON-F	RESET (POR) VOLTAGE THRESH	OLD					
	VIN POR Voltage Threshold	V <sub>IN</sub> rising	3.9	4.1	4.3	V	
	VIN POR Hysteresis		-	0.5	-	V	
REFERENCE	VOLTAGE						
$V_{REF}$	Reference Voltage	Regulated on FB pin	-	0.8	-	V	
	Output Voltage Accuracy	$T_J = 25^{\circ}C$ , $I_{OUT} = 10$ mA, $V_{IN} = 12$ V	-1.0	-	+1.0	%	
	Output Voltage Accuracy	I <sub>OUT</sub> =10mA~3A, V <sub>IN</sub> =4.75~14V	-2.0	-	+2.0	76	
	Line Regulation	V <sub>IN</sub> = 4.75V to 14V	-	+0.02	-	%/V	
	Load Regulation	I <sub>OUT</sub> = 0.5A ~ 3A	-	-0.04	-	%/A	

Note 3: The case temperature is measured at the center of the exposed pad on the underside of the SOP-8P and DFN4x4-8 packages.



# **Electrical Characteristics (Cont.)**

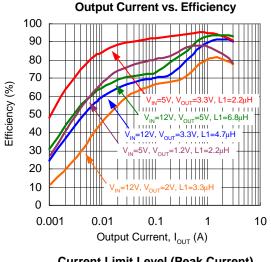
Refer to the "Typical Application Circuits". These specifications apply over  $V_{IN}$ =12V,  $V_{OUT}$ =3.3V and  $T_A$ = -40 ~ 85°C, unless otherwise specified. Typical values are at  $T_A$ =25°C.

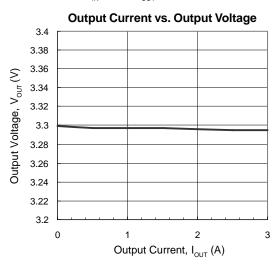
Symbol	Parameter	Test Conditions		Unit		
Symbol	Parameter	rest Conditions	Min.	Тур.	Max.	Unit
OSCILLATOR	AND DUTY CYCLE		•	•		
Fosc	Oscillator Frequency	$T_J = -40 \sim 125^{\circ}C$ , $V_{IN} = 4.75 \sim 14V$	450	500	550	kHz
	Foldback Frequency	V <sub>OUT</sub> = 0V	-	80	-	kHz
	Maximum Converter's Duty		-	99	-	%
T <sub>ON_MIN</sub>	Minimum Pulse Width of LX		-	150	-	ns
CURRENT-MO	ODE PWM CONVERTER	•	•			,
Gm	Error Amplifier Transconductance	V <sub>FB</sub> =V <sub>REF</sub> ±50mV	-	200	-	μA/V
	Error Amplifier DC Gain	COMP = NC	-	80	-	dB
	Current-Sense to COMP Voltage Transresistance		-	0.1	-	V/A
		Between VIN and Exposed Pad, $V_{IN} = 5V$ , $T_J=25^{\circ}C$	-	70	100	
	High-Side Switch Resistance	Between VIN and Exposed Pad, V <sub>IN</sub> = 12V, T <sub>J</sub> =25°C	-	55	80	mΩ
		Between GND and Exposed Pad, V <sub>IN</sub> = 5V, T <sub>J</sub> =25°C	-	55	100	
	Low-Side Switch Resistance	Between GND and Exposed Pad, V <sub>IN</sub> = 12V, T <sub>J</sub> =25°C	-	45	80	mΩ
PROTECTION	IS					
I <sub>LIM</sub>	High-Side Switch Current-limit	Peak Current	5	6.5	8	Α
$V_{TH\_UV}$	FB Under-Voltage Threshold	V <sub>FB</sub> falling	45	50	55	%
$V_{TH\_OV}$	FB Over-Voltage Threshold	V <sub>FB</sub> rising	118	123	128	%
	FB Under-Voltage Debounce		-	1	-	μs
T <sub>OTP</sub>	Over-Temperature Trip Point		-	150	-	°C
	Over-Temperature Hysteresis		-	40	-	°C
T <sub>D</sub>	Dead-Time	V <sub>LX</sub> = -0.7V	-	20	-	ns
OFT-START	, SOFT-STOP, ENABLE, AND INPUT (	CURRENTS				
$T_{SS}$	Soft-Start / Soft-Stop Interval		1.5	2	2.5	ms
	EN Low Logic Level	V <sub>EN</sub> falling	_	-	0.5	V
	EN High Logic Level	V <sub>EN</sub> rising	2.1	-	-	V
	High-side Switch Leakage Current	$V_{EN} = 0V$ , $V_{LX} = 0V$	-	-	2	μΑ
I <sub>FB</sub>	FB Pin Input Current		-100	-	+100	nA
I <sub>EN</sub>	EN Pin Input Current	$V_{EN} = 0V \sim V_{IN}$	-100	-	+100	nA

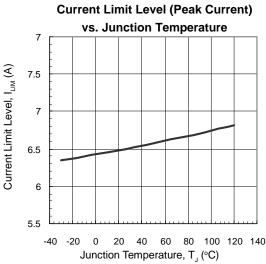


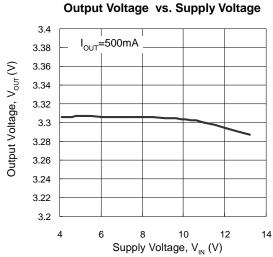
## **Typical Operating Characteristics**

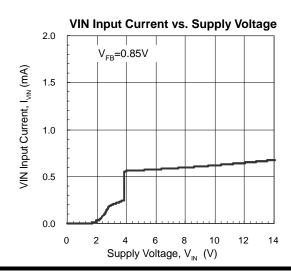
(Refer to the application circuit 1 in the section "Typical Application Circuits",  $V_{IN}$ =12V,  $V_{OUT}$ =3.3V, L1=4.7 $\mu$ H)

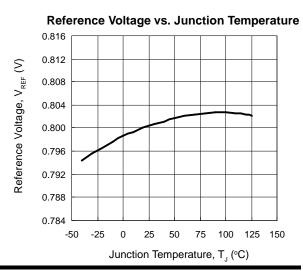








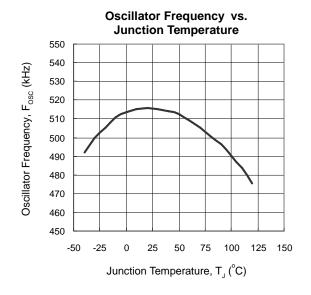






# **Typical Operating Characteristics (Cont.)**

(Refer to the application circuit 1 in the section "Typical Application Circuits",  $V_{IN}$ =12V,  $V_{OUT}$ =3.3V, L1=4.7 $\mu$ H)

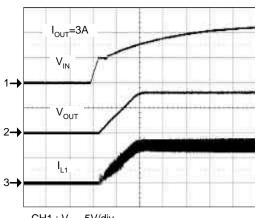




# **Operating Waveforms**

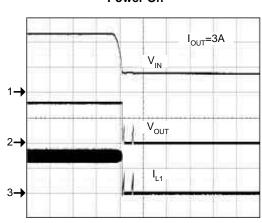
(Refer to the application circuit 1 in the section "Typical Application Circuits",  $V_{IN}$ =12V,  $V_{OUT}$ =3.3V, L1=4.7 $\mu$ H)

#### Power On



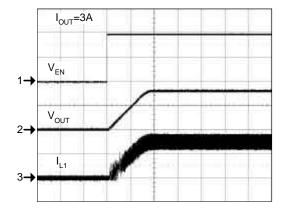
 $\begin{array}{l} \text{CH1: V}_{\text{IN}} \text{ , 5V/div} \\ \text{CH2: V}_{\text{OUT}}, \text{2V/div} \\ \text{CH3: I}_{\text{L1}}, \text{2A/div} \\ \text{Time: 1ms/div} \end{array}$ 

#### **Power Off**



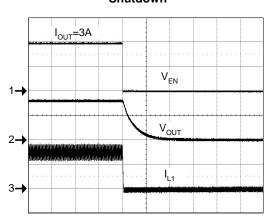
 $\begin{array}{l} \text{CH1}: \textbf{V}_{\text{IN}} \text{, 5V/div} \\ \text{CH2}: \textbf{V}_{\text{OUT}} \text{, 2V/div} \\ \text{CH3}: \textbf{I}_{\text{L1}} \text{, 2A/div} \\ \text{Time}: 10\text{ms/div} \end{array}$ 

### Enable



 $\begin{array}{l} \text{CH1: V}_{\text{EN}} \text{ , 5V/div} \\ \text{CH2: V}_{\text{OUT}} \text{ , 2V/div} \\ \text{CH3: I}_{\text{L1}} \text{ , 2A/div} \\ \text{Time: 1ms/div} \end{array}$ 

## Shutdown



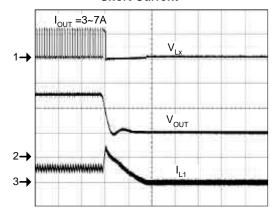
 $\begin{array}{l} CH1: V_{EN} \ , 5V/div \\ CH2: V_{OUT} \ , 2V/div \\ CH3: I_{L1}, \ 2A/div \\ Time: 100 \mu s/div \end{array}$ 



# **Operating Waveforms (Cont.)**

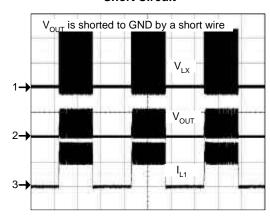
(Refer to the application circuit 1 in the section "Typical Application Circuits",  $V_{IN}$ =12V,  $V_{OUT}$ =3.3V, L1=4.7 $\mu$ H)

#### **Short Current**



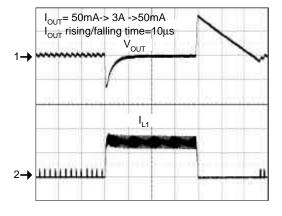
 $\begin{array}{l} CH1: V_{LX} \,,\, 10V/div \\ CH2: V_{OUT} \,,\, 2V/div \\ CH3: I_{L1} \,,\, 5A/div \\ Time: 20 \mu s/div \end{array}$ 

#### **Short Circuit**



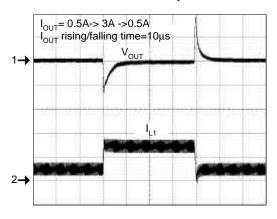
$$\label{eq:charge_continuity} \begin{split} & \text{CH1: V}_{\text{LX}} \text{ , 5V/div} \\ & \text{CH2: V}_{\text{OUT}} \text{ , 200mV/div} \\ & \text{CH3: I}_{\text{L1}} \text{ , 5A/div} \\ & \text{Time: 5ms/div} \end{split}$$

### **Load Transient Response**



 $\begin{aligned} &CH1: V_{OUT} \text{ , } 200mV/div} \\ &CH2: I_{L1} \text{ , } 2A/div} \\ &Time: 100\mu\text{s/div} \end{aligned}$ 

#### **Load Transient Response**



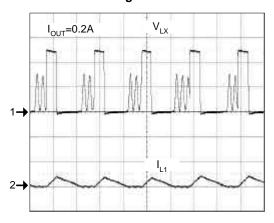
 $\begin{aligned} & \text{CH1:V}_{\text{OUT}} \text{ , } 100\text{mV/div} \\ & \text{CH2:I}_{\text{L1}} \text{ , } 2\text{A/div} \\ & \text{Time:100} \mu\text{s/div} \end{aligned}$ 



# **Operating Waveforms (Cont.)**

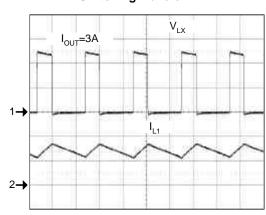
(Refer to the application circuit 1 in the section "Typical Application Circuits",  $V_{IN}$ =12V,  $V_{OUT}$ =3.3V, L1=4.7 $\mu$ H)

### **Switching Waveform**



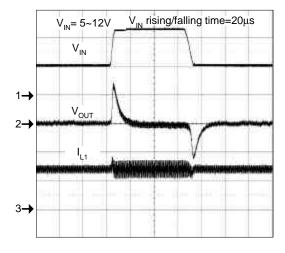
 $CH1: V_{LX} \ , \ 5V/div$   $CH2: I_{L1} \ , \ 2A/div$   $Time: 1\mu s/div$ 

### **Switching Waveform**



 $\begin{aligned} &\text{CH1:V}_{\text{LX}}\,,\,5\text{V/div}\\ &\text{CH2:I}_{\text{L1}}\,,\,2\text{A/div}\\ &\text{Time:1}\mu\text{s/div} \end{aligned}$ 

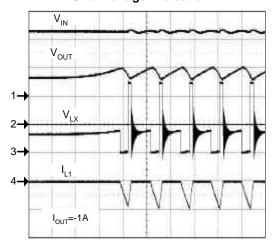
#### **Line Transient**



 $\mathrm{CH1}: \mathrm{V}_{\mathrm{IN}}$  , 5V/div

Time: 100µs/div

#### **Over-Voltage Protection**



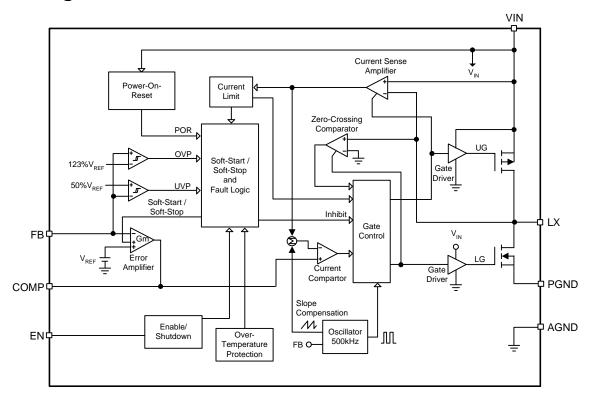
 $\begin{array}{l} \text{CH1}: \text{V}_{\text{IN}} \text{ , 5V/div} \\ \text{CH2}: \text{V}_{\text{OUT}} \text{ , 2V/div} \\ \text{CH3}: \text{V}_{\text{LX}} \text{ , 5V/div} \\ \text{CH4}: \text{I}_{\text{L1}} \text{ , 5A/div} \\ \text{Time}: 20 \mu \text{s/div} \end{array}$ 



# **Pin Description**

Р	IN	FUNCTION
NO.	NAME	FUNCTION
1	NC	No Connection.
2	VIN	Power Input. VIN supplies the power (4.3V to 14V) to the control circuitry, gate drivers and step-down converter switches. Connecting a ceramic bypass capacitor and a suitably large capacitor between VIN and both of AGND and PGND to eliminate switching noise and voltage ripple on the input to the IC.
3	AGND	Ground of MOSFET Gate Drivers and Control Circuitry.
4	FB	Output Feedback Input. The APW7145 senses the feedback voltage via FB and regulates the voltage at 0.8V. Connecting FB with a resistor-divider from the converter's output sets the output voltage from 0.8V to VIN.
5	COMP	Output of the error amplifier. Connecting a series RC network from COMP to GND to compensate the regulation control loop. In some cases, an additional capacitor from COMP to GND is required.
6	EN	Enable Input. EN is a digital input that turns the regulator on or off. Drive EN high to turn on the regulator, drive it low to turn it off. Connecting this pin to VIN if it is not used.
7	LX	Power Switching Output. LX is the junction of the high-side and low-side power MOSFETs to supply power to the output LC filter.
8	PGND	Power Ground of the APW7145, which is the source of the N-channel power MOSFET. Connect this pin to the system ground with lowest impedance.
9 (Exposed Pad)	LX	Power Switching Output. LX is the Drain of the P-channel MOSFET to supply power to the output. The Exposed Pad provides current with lower impedance than the Pin 7. Connecting the pad to output LC filter via a top-layer thermal pad on PCBs. The PCB will be a heat sink of the IC.

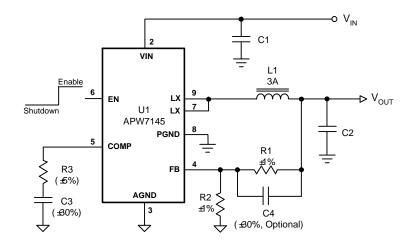
# **Block Diagram**





# **Typical Application Circuit**

### 1. 4.3~14V Single Power Input Step-down Converter (with a Ceramic Output Capacitor)



#### a. Cost-effective Feedback Compensation (C4 is no connection)

V <sub>IN</sub> (V)	V <sub>OUT</sub> (V)	L1(μF)	C2(μF)	C2 ESR(mΩ)	R1(kΩ)	R2(kΩ)	R3(kΩ)	C3(pF)
12	5	6.8	22	5	63.0	12	33.0	820
12	5	6.8	44	3	63.0	12	68.0	820
12	3.3	4.7	22	5	46.9	15	27.0	1000
12	3.3	4.7	44	3	46.9	15	56.0	1000
12	2	3.3	22	5	30.0	20	18.0	1800
12	2	3.3	44	3	30.0	20	33.0	1800
12	1.8	3.3	22	5	18.8	15	15.0	1800
12	1.8	3.3	44	3	18.8	15	30.0	1800
5	3.3	2.2	22	5	46.9	15	27.0	470
5	3.3	2.2	44	3	46.9	15	56.0	470
5	1.8	2.2	22	5	25.0	20	15.0	820
5	1.8	2.2	44	3	25.0	20	30.0	820
5	1.5	2.2	22	5	21.9	25	12.0	1000
5	1.5	2.2	44	3	21.9	25	24.0	1000
5	1.2	2.2	22	5	7.5	15	10.0	1200
5	1.2	2.2	44	3	7.5	15	20.0	1200

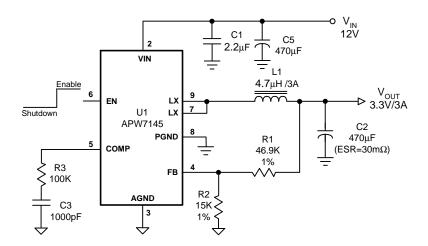


# **Typical Application Circuit (Cont.)**

b. Fast-Transient-Response Feedback Compensation (C4 is connected)

V <sub>IN</sub> (V)	V <sub>OUT</sub> (V)	L1(μH)	C2(μF)	C2 ESR(mΩ)	R1(kΩ)	R2(kΩ)	R3(kΩ)	C3(pF)	C4(pF)
12	5	6.8	22	5	63.0	12	43	680.0	27
12	5	6.8	44	3	63.0	12	82	680.0	27
12	3.3	4.7	22	5	46.9	15	27	1000.0	27
12	3.3	4.7	44	3	46.9	15	56	1000.0	27
12	2	3.3	22	5	30.0	20	18	1800.0	27
12	2	3.3	44	3	30.0	20	33	1800.0	27
12	1.8	3.3	22	5	18.8	15	15	1800.0	33
12	1.8	3.3	44	3	18.8	15	30	1800.0	33
5	3.3	2.2	22	5	46.9	15	27	470.0	27
5	3.3	2.2	44	3	46.9	15	56	470.0	27
5	1.8	2.2	22	5	25.0	20	15	820.0	56
5	1.8	2.2	44	3	25.0	20	30	820.0	56
5	1.5	2.2	22	5	22	25	12	1000	56
5	1.5	2.2	44	3	22	25	24	1000	56
5	1.2	2.2	22	5	7.5	15	10	1200	180
5	1.2	2.2	44	3	7.5	15	20	1200	270

### 2. +12V Single Power Input Step-down Converter (with an Electrolytic Output Capacitor)





## **Function Description**

#### VIN Power-On-Reset (POR)

The APW7145 keeps monitoring the voltage on the VIN pin to prevent wrong logic operations which may occur when VIN voltage is not high enough for the internal control circuitry to operate. The VIN POR has a rising threshold of 4.1V (typical) with 0.5V of hysteresis.

During start-up, the VIN voltage must exceed the enable voltage threshold. Then, the IC starts a start-up process and ramps up the output voltage to the voltage target.

#### **Digital Soft-Start**

The APW7145 has a built-in digital soft-start to control the rise rate of the output voltage and limit the input current surge during start-up. During soft-start, an internal voltage ramp ( $V_{\text{RAMP}}$ ), connected to one of the positive inputs of the error amplifier, rises up from 0V to 0.95V to replace the reference voltage (0.8V) until the voltage ramp reaches the reference voltage.

During soft-start without output over-voltage, the APW7145 converter's sinking capability is disabled until the output voltage reaches the voltage target.

#### **Digital Soft-Stop**

At the moment of shutdown controlled by EN signal, under-voltage event, or over-temperature protection, the APW7145 initiates a digital soft-stop process to discharge the output voltage in the output capacitors. Certainly, the load current also discharges the output voltage.

During soft-stop, the internal voltage ramp ( $V_{RAMP}$ ) falls down from 0.95V to 0V to replace the reference voltage. Therefore, the output voltage falls down slowly at light load. After the soft-stop interval elapses, the soft-stop process ends and the the IC turns on the low-side power MOSFET.

#### **Output Under-Voltage Protection (UVP)**

In the operational process, if a short-circuit occurs, the output voltage will drop quickly. Before the current-limit circuit responds, the output voltage will fall out of the required regulation range. The under-voltage continually monitors the FB voltage after soft-start is completed. If a load step is strong enough to pull the output voltage lower than the under-voltage threshold, the IC shuts down converter's output.

The under-voltage threshold is 50% of the nominal output voltage. The undervoltage comparator has a built-in 2µs noise filter to prevent the chips from wrong UVP shutdown caused by noise. The under-voltage protection works in a hiccup mode without latched shutdown. The IC will initiate a new soft-start process at the end of the preceding delay.

#### Over-Voltage Protection (OVP)

The over-voltage function monitors the output voltage by FB pin. When the FB voltage increase over 123% of the reference voltage due to the high-side MOSFET failure, or for other reasons, the over-voltage protection comparator will force the low-side MOSFET gate driver high. This action actively pulls down the output voltage and eventually attempts to blow the internal bonding wires. As soon as the output voltage is within regulation, the OVP comparator is disengaged. The chip will restore its normal operation. This OVP scheme only clamps the voltage overshoot and does not invert the output voltage when otherwise activated with a continuously high output from low-side MOSFET driver - a common problem for OVP schemes with a latch.

#### **Over-Temperature Protection (OTP)**

The over-temperature circuit limits the junction temperature of the APW7145. When the junction temperature exceeds  $T_J$  = +150°C, a thermal sensor turns off the both power MOSFETs, allowing the devices to cool. The thermal sensor allows the converters to start a start-up process and regulate the output voltage again after the junction temperature cools by 40°C. The OTP is designed with a 40°C hysteresis to lower the average  $T_J$  during continuous thermal overload conditions, increasing lifetime of the APW7145.

#### Enable/Shutdown

Driving EN to the ground initiates a soft-stop process and then places the APW7145 in shutdown. When in shutdown, after the soft-stop process is completed, the internal power MOSFETs turns off, all internal circuitry shuts down and the quiescent supply current reduces to less than 3mA.



# **Function Description (Cont.)**

#### **Current-Limit Protection**

The APW7145 monitors the output current, flowing through the high-side power MOSFET, and limits the current peak at current-limit level to prevent loads and the IC from damages during overload or short-circuit conditions.

### Frequency Foldback

The foldback frequency is controlled by the FB voltage. When the output is shortened to the ground, the frequency of the oscillator will be reduced to 80kHz. This lower frequency allows the inductor current to safely discharge, thereby preventing current runaway. The oscillator's frequency will gradually increase to its designed rate when the feedback voltage on FB again approaches 0.8V.



## **Application Information**

#### **Setting Output Voltage**

The regulated output voltage is determined by:

Vout = 
$$0.8 \cdot (1 + \frac{R1}{R2})$$
 (V)

Suggested R2 is in the range from 1K to  $20k\Omega$ . For portable applications, a 10K resistor is suggested for R2. To prevent stray pickup, please locate resistors R1 and R2 close to APW7145.

#### **Input Capacitor Selection**

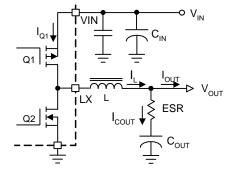
Use small ceramic capacitors for high frequency decoupling and bulk capacitors to supply the surge current needed each time the P-channel power MOSFET (Q1) turns on. Place the small ceramic capacitors physically close to the VIN and between the VIN and the GND.

The important parameters for the bulk input capacitor are the voltage rating and the RMS current rating. For reliable operation, select the bulk capacitor with voltage and current ratings above the maximum input voltage and largest RMS current required by the circuit. The capacitor voltage rating should be at least 1.25 times greater than the maximum input voltage and a voltage rating of 1.5 times is a conservative guideline. The RMS current (I<sub>RMS</sub>) of the bulk input capacitor is calculated as the following equation:

IRMS = IOUT 
$$\cdot \sqrt{D \cdot (1-D)}$$
 (A)

where D is the duty cycle of the power MOSFET.

For a through hole design, several electrolytic capacitors may be needed. For surface mount designs, solid tantalum capacitors can be used, but caution must be exercised with regard to the capacitor surge current rating.



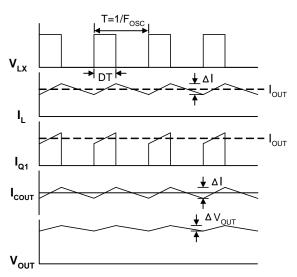


Figure 1. Converter Waveforms

#### **Output Capacitor Selection**

An output capacitor is required to filter the output and supply the load transient current. The filtering requirements are the function of the switching frequency and the ripple current ( $\Delta$ I). The output ripple is the sum of the voltages, having phase shift, across the ESR, and the ideal output capacitor. The peak-to-peak voltage of the ESR is calculated as the following equations:

$$D = \frac{V_{OUT}}{V_{IN}} \qquad .....(1)$$

$$V_{ESR} = \Delta I \cdot ESR$$
 .....(3

The peak-to-peak voltage of the ideal output capacitor is calculated as the following equation:

For the applications using bulk capacitors, the  $\Delta V_{\text{COUT}}$  is much smaller than the  $V_{\text{ESR}}$  and can be ignored. Therefore, the AC peak-to-peak output voltage ( $\Delta V_{\text{OUT}}$ ) is shown as below:

$$\Delta V_{OUT} = \Delta I \cdot ESR$$
 (V) ............ (5



# **Application Information (Cont.)**

#### **Output Capacitor Selection (Cont.)**

For the applications using ceramic capacitors, the V $_{\rm ESR}$  is much smaller than the  $\Delta V_{\rm COUT}$  and can be ignored. Therefore, the AC peak-to-peak output voltage ( $\Delta V_{\rm OUT}$ ) is close to  $\Delta V_{\rm COUT}$ .

The load transient requirements are the function of the slew rate (di/dt) and disengaged\the magnitude of the transient load current. These requirements are generally met with a mix of capacitors and careful layout. High frequency capacitors initially supply the transient and slow the current load rate seen by the bulk capacitors. The bulk filter capacitor values are generally determined by the ESR (Effective Series Resistance) and voltage rating requirements rather than actual capacitance requirements.

High frequency decoupling capacitors should be placed as close to the power pins of the load as physically possible. Be careful not to add inductance in the circuit board wiring that could cancel the usefulness of these low inductance components. An aluminum electrolytic capacitor's ESR value is related to the case size with lower ESR available in larger case sizes. However, the Equivalent Series Inductance (ESL) of these capacitors increases with case size and can reduce the usefulness of the capacitor to high slew-rate transient loading.

#### Inductor Value Calculation

The operating frequency and inductor selection are interrelated in that higher operating frequencies permit the use of a smaller inductor for the same amount of inductor ripple current. However, this is at the expense of efficiency due to an increase in MOSFET gate charge losses. The equation (2) shows that the inductance value has a direct effect on ripple current.

Accepting larger values of ripple current allows the use of low inductances, but results in higher output voltage ripple and greater core losses. A reasonable starting point for setting ripple current is  $\Delta I \leq 0.4 \cdot I_{\text{OUT(MAX)}}$ . Please be noticed that the maximum ripple current occurs at the maximum input voltage. The minimum inductance of the inductor is calculated by using the following equation:

$$\begin{split} &\frac{V_{\text{OUT}} \cdot (V_{\text{IN}} - V_{\text{OUT}})}{500000 \cdot L \cdot V_{\text{IN}}} \leq 1.2 \\ &L \geq \frac{V_{\text{OUT}} \cdot (V_{\text{IN}} - V_{\text{OUT}})}{600000 \cdot V_{\text{IN}}} \qquad \text{(H)} \qquad \qquad \dots \dots \dots \text{(6)} \end{split}$$
 where  $V_{\text{IN}} = V_{\text{IN(MAX)}}$ 

#### **Layout Consideration**

In high power switching regulator, a correct layout is important to ensure proper operation of the regulator. In general, interconnecting impedance should be minimized by using short and wide printed circuit traces. Signal and power grounds are to be kept separating and finally combined using ground plane construction or single point grounding. Figure 2 illustrates the layout, with bold lines indicating high current paths. Components along the bold lines should be placed close together. Below is a checklist for your layout:

 Firstly, to initial the layout by placing the power components. Orient the power circuitry to achieve a clean power flow path. If possible, make all the connections on one side of the PCB with wide and copper filled areas.

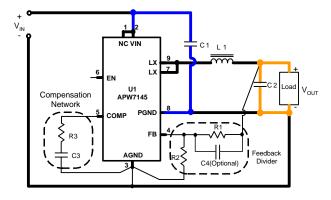


Figure 2. Current Path Diagram

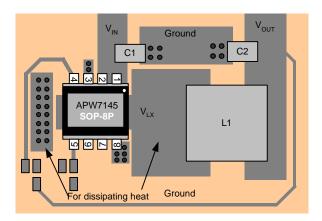
In Figure 2, the loops with same color bold lines conduct high slew rate current. These interconnecting impedances should be minimized by using wide and short printed circuit traces.



## **Application Information (Cont.)**

#### **Layout Consideration (Cont.)**

- 3. Keep the sensitive small signal nodes (FB and COMP) away from switching nodes (LX or others) on the PCB. Therefore, place the feedback divider and the feedback compensation network close to the IC to avoid switching noise. Connect the ground of feedback divider directly to the AGND pin of the IC using a dedicated ground trace.
- 4. Place the decoupling ceramic capacitor C1 near the VIN as close as possible. Use a wide power ground plane to connect the C1 and C2 to provide a low impedance path between the components for large and high slew rate current.



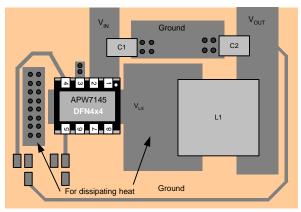
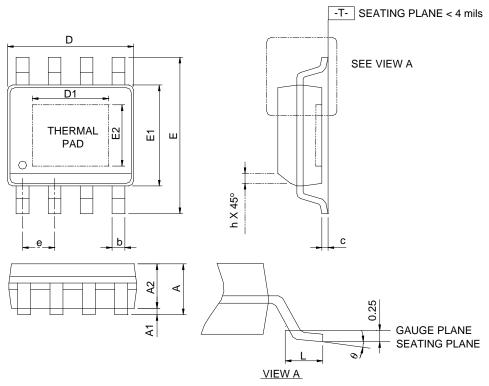


Figure 3. Recommended Layout Diagram



# **Package Information**

#### SOP-8P



ş	SOP-8P								
%¥ <b>№</b>	MILLIM	ETERS	INC	HES					
2	MIN.	MAX.	MIN.	MAX.					
A		1.60		0.063					
A1	0.00	0.15	0.000	0.006					
A2	1.25		0.049						
b	0.31	0.51	0.012	0.020					
С	0.17	0.25	0.007	0.010					
D	4.80	5.00	0.189	0.197					
D1	2.50	3.50	0.098	0.138					
Е	5.80	6.20	0.228	0.244					
E1	3.80	4.00	0.150	0.157					
E2	2.00	3.00	0.079	0.118					
е	1.27	BSC	0.05	0 BSC					
h	0.25	0.50	0.010	0.020					
L	0.40	1.27	0.016	0.050					
θ	0°C	8°C	0°C	8°C					

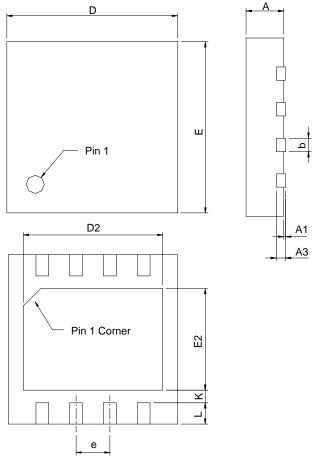
Note: 1. Followed from JEDEC MS-012 BA.

- 2. Dimension "D" does not include mold flash, protrusions or gate burrs. Mold flash, protrusion or gate burrs shall not exceed 6 mil per side .
- 3. Dimension "E" does not include inter-lead flash or protrusions.
  Inter-lead flash and protrusions shall not exceed 10 mil per side.



# **Package Information**

### DFN4x4-8

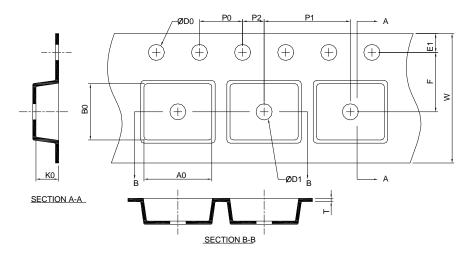


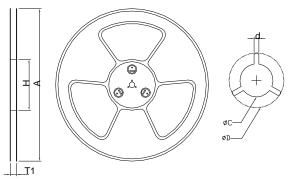
ş				
SY MBOL	MILLIM	ETERS	INC	HES
<u>۲</u>	MIN.	MAX.	MIN.	MAX.
Α	0.80	1.00	0.031	0.039
A1	0.00	0.05	0.000	0.002
АЗ	0.20	REF	0.00	8 REF
b	0.25	0.35	0.010	0.014
D	3.90	4.10	0.154	0.161
D2	3.10	3.30	0.122	0.130
Е	3.90	4.10	0.154	0.161
E2	2.40	2.60	0.094	0.102
е	0.80 BSC		0.03	1 BSC
L	0.40	0.60	0.016	0.024
K	0.20		0.008	

Note: 1. Followed from JEDEC MO-229 VGGB.



# **Carrier Tape & Reel Dimensions**





Application	Α	Н	T1	С	d	D	W	E1	F
	330.0 £.00	50 MIN.	12.4+2.00 -0.00	13.0+0.50 -0.20	1.5 MIN.	20.2 MIN.	12.0 <b>£</b> 0.30	1.75 ±0.10	5.5 <b>±</b> 0.05
SOP-8P	P0	P1	P2	D0	D1	Т	A0	В0	K0
	4.0 <b>±</b> 0.10	8.0 <b>±</b> 0.10	2.0 <b>±</b> 0.05	1.5+0.10 -0.00	1.5 MIN.	0.6+0.00 -0.40	6.40 <b>£</b> 0.20	5.20 <b>£</b> 0.20	2.10 <b>±</b> 0.20
Application	Α	Н	T1	С	d	D	W	E1	F
	330.0 £.00	50 MIN.	12.4+2.00 -0.00	13.0+0.50 -0.20	1.5 MIN.	20.2 MIN.	12.0 <b>±</b> 0.30	1.75 ±0.10	5.5 <b>±</b> 0.05
DFN4x4-8	P0	P1	P2	D0	D1	Т	A0	В0	K0
	4.0 <b>±</b> 0.10	8.0 ±0.10	2.0 ±0.05	1.5+0.10 -0.00	1.5 MIN.	0.6+0.00 -0.40	4.30 ±0.20	4.30 ±0.20	1.30 ±0.20

(mm)

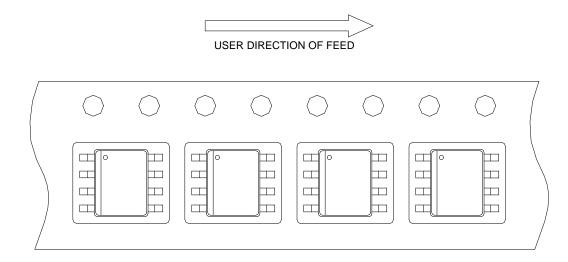
# **Devices Per Unit**

Package Type	Unit	Quantity
SOP-8P	Tape & Reel	2500
DFN4x4-8	Tape & Reel	3000

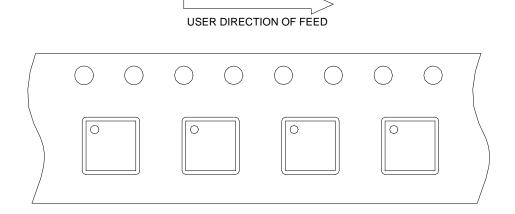


# **Taping Direction Information**

SOP-8P

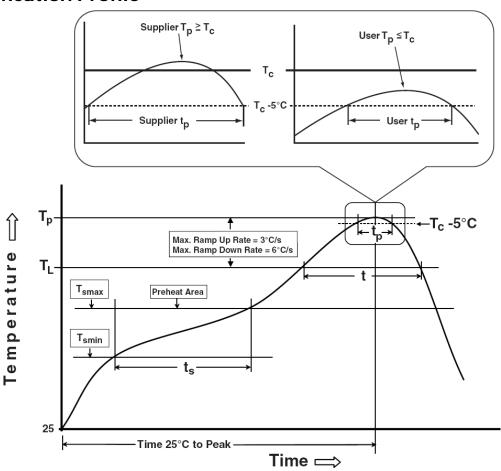


## DFN4x4-8





## **Classification Profile**



## **Classification Reflow Profiles**

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly	
Preheat & Soak Temperature min (T <sub>smin</sub> ) Temperature max (T <sub>smax</sub> ) Time (T <sub>smin</sub> to T <sub>smax</sub> ) (t <sub>s</sub> )	100 °C 150 °C 60-120 seconds	150 °C 200 °C 60-120 seconds	
Average ramp-up rate (T <sub>smax</sub> to T <sub>P</sub> )	3 °C/second max.	3°C/second max.	
Liquidous temperature (T <sub>L</sub> ) Time at liquidous (t <sub>L</sub> )	183 °C 60-150 seconds	217 °C 60-150 seconds	
Peak package body Temperature (T <sub>p</sub> )*	See Classification Temp in table 1	See Classification Temp in table 2	
Time $(t_P)^{**}$ within 5°C of the specified classification temperature $(T_c)$	20** seconds	30** seconds	
Average ramp-down rate (Tp to Tsmax)	6 °C/second max.	6 °C/second max.	
Time 25°C to peak temperature	6 minutes max.	8 minutes max.	

<sup>\*</sup> Tolerance for peak profile Temperature (Tp) is defined as a supplier minimum and a user maximum.

<sup>\*</sup> Tolerance for time at peak profile temperature (tp) is defined as a supplier minimum and a user maximum.



## **Classification Reflow Profiles (Cont.)**

Table 1. SnPb Eutectic Process – Classification Temperatures (Tc)

Package Thickness	Volume mm <sup>3</sup> <350	Volume mm <sup>3</sup> <sup>3</sup> 350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (Tc)

Package	Volume mm <sup>3</sup>	Volume mm <sup>3</sup>	Volume mm <sup>3</sup>
Thickness	<350	350-2000	>2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

## **Reliability Test Program**

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
HOLT	JESD-22, A108	1000 Hrs, Bias @ T <sub>j</sub> =125°C
PCT	JESD-22, A102	168 Hrs, 100%RH, 2atm, 121°C
тст	JESD-22, A104	500 Cycles, -65°C~150°C
НВМ	MIL-STD-883-3015.7	VHBM 2KV
MM	JESD-22, A115	VMM 200V
Latch-Up	JESD 78	10ms, 1 <sub>tr</sub> 100mA

## **Customer Service**

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